

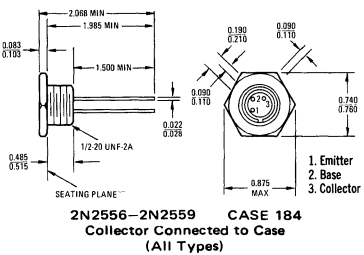
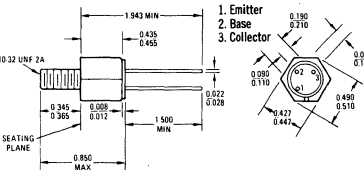
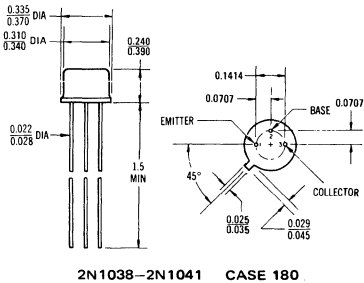
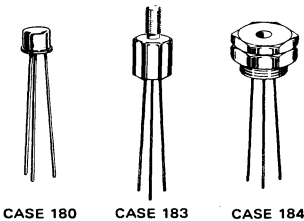
2N1038 thru 2N1041 (GERMANIUM)
2N2552 thru 2N2559

PNP GERMANIUM MEDIUM POWER TRANSISTORS

... designed for relay drivers, pulse amplifiers, audio amplifiers and high-current switching applications.

- High Current Capability – $I_C = 3.0$ Amperes
- Guaranteed Excellent Collector-Emitter Sustaining Voltage
- 20-Watt Power Dissipation at 25°C Case Temperature
- 100°C Maximum Junction Temperature

PNP GERMANIUM
POWER TRANSISTORS
40–100 VOLTS
20 WATTS



*MAXIMUM RATINGS

Rating	Symbol	2N1038 2N2552 2N2556	2N1039 2N2553 2N2557	2N1040 2N2554 2N2558	2N1041 2N2555 2N2559	Unit
Collector-Emitter Voltage	V_{CEO}	30	40	50	60	Vdc
Collector-Base Voltage	V_{CB}	40	60	80	100	Vdc
Emitter-Base Voltage	V_{EB}	20				Vdc
Collector Current – Continuous	I_C	3.0				Adc
Base Current – Continuous	I_B	1.0				Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	450 6.0				mW mW/°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C (Note 1)	P_D	20 0.267				Watts W/°C
**Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +100				°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	3.75	°C/W

*Indicates JEDEC Registered Data.
Note 1: Case Temperature shall be measured 0.100 ± 0.010 inches above the seating plane.
**Motorola guarantees this data in addition to the JEDEC Registered Data shown.

2N1038 thru 2N1041/2N2552 thru 2N2559 (continued)

*ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage ($I_C = 100\text{ mAdc}$, $I_B = 0$)	$V_{CE(sus)}$	30 40 50 60	- - - -	Vdc
Collector Cutoff Current ($V_{CE} = 15\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 20\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 25\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$)	I_{CEO}	- - - -	25 20 20 20	mAdc
Collector-Emitter Cutoff Current ($V_{CE} = 40\text{ Vdc}$, $V_{BE(off)} = 0.2\text{ Vdc}$) ($V_{CE} = 60\text{ Vdc}$, $V_{BE(off)} = 0.2\text{ Vdc}$) ($V_{CE} = 80\text{ Vdc}$, $V_{BE(off)} = 0.2\text{ Vdc}$) ($V_{CE} = 100\text{ Vdc}$, $V_{BE(off)} = 0.2\text{ Vdc}$) ($V_{CE} = 20\text{ Vdc}$, $V_{BE(off)} = 0.2\text{ Vdc}$, $T_C = 85^\circ\text{C}$) ($V_{CE} = 30\text{ Vdc}$, $V_{BE(off)} = 0.2\text{ Vdc}$, $T_C = 85^\circ\text{C}$) ($V_{CE} = 40\text{ Vdc}$, $V_{BE(off)} = 0.2\text{ Vdc}$, $T_C = 85^\circ\text{C}$) ($V_{CE} = 50\text{ Vdc}$, $V_{BE(off)} = 0.2\text{ Vdc}$, $T_C = 85^\circ\text{C}$)	I_{CEX}	- - - - - - - -	0.65 0.65 0.65 0.65 5.0 5.0 5.0 5.0	mAdc
Collector Cutoff Current ($V_{CB} = 20\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 30\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 40\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 50\text{ Vdc}$, $I_E = 0$) **($V_{CB} = 40\text{ Vdc}$, $I_E = 0$) **($V_{CB} = 60\text{ Vdc}$, $I_E = 0$) **($V_{CB} = 80\text{ Vdc}$, $I_E = 0$) **($V_{CB} = 100\text{ Vdc}$, $I_E = 0$)	I_{CBO}	- - - - - - - -	125 125 125 125 750 750 750 750	μAdc
Emitter Cutoff Current ($V_{BE} = 20\text{ Vdc}$, $I_C = 0$)	I_{EBO}	-	650	μAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 50\text{ mAdc}$, $V_{CE} = 0.5\text{ Vdc}$) ($I_C = 1.0\text{ Adc}$, $V_{CE} = 0.5\text{ Vdc}$)	h_{FE}	33 20	200 60	-
Collector-Emitter Saturation Voltage ($I_C = 1.0\text{ Adc}$, $I_B = 100\text{ mAdc}$)	$V_{CE(sat)}$	-	0.25	Vdc
Base-Emitter Input Voltage ($I_C = 1.0\text{ Adc}$, $V_{CE} = 0.5\text{ Vdc}$)	V_{BE}	-	1.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

Small-Signal Current Gain ($I_C = 500\text{ mAdc}$, $V_{CE} = 1.5\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	18	72	-
Small-Signal Current Gain ($I_C = 500\text{ mAdc}$, $V_{CE} = 1.5\text{ Vdc}$, $f = 112.5\text{ kHz}$)	$ h_{fe} $	2.0	-	-

*Indicates JEDEC Registered Data.

**Motorola Guarantees this data in addition to the JEDEC Registered Data Shown.